PF01410A

MOS FET Power Amplifier Module for GSM Handy Phone

HITACHI

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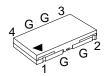
Application

• For GSM class4 890 to 915 MHz

Features

- 4.8 V operation 2 stage amplifier
- Small package
- High efficiency: 45% Typ
- High speed switching: 1 μsec

Pin Arrangement



- 1: Pin
 - 2: Vapc
- 3. Nqq
- 4: Pout
- G: GND

Absolute Maximum Ratings (Tc = 25°C)

Item	Symbol	Rating	Unit	
Supply voltage	V_{DD}	10	V	
Supply current	I _{DD}	3	А	
V _{APC} voltage	V _{APC}	4	V	
Input power	Pin	50	mW	
Operating case temperature	Tc (op)	-30 to +100	°C	
Storage temperature	Tstg	-30 to +100	°C	
Output power	Pout	4	W	

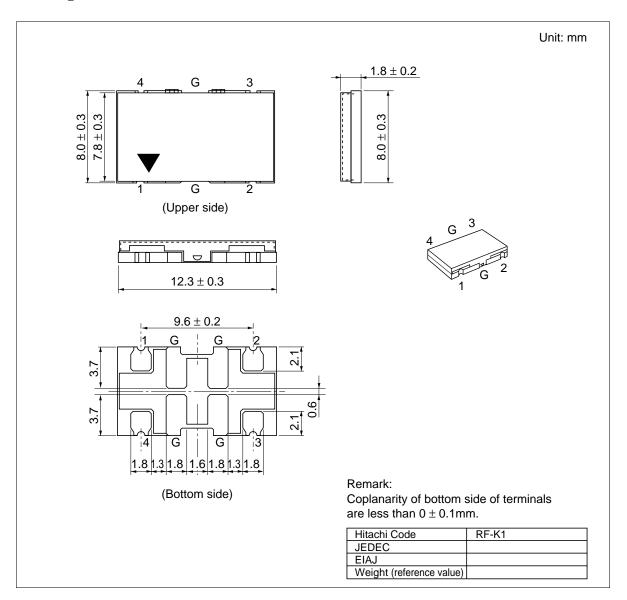


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Electrical Characteristics ($Tc = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Frequency range	f	890	_	915	MHz	_
Control voltage range	V_{APC}	0.1	_	2.5	V	_
Drain cutoff current	I _{DS}	_	_	100	μΑ	V _{DD} = 10 V, V _{APC} = 0 V
Total efficiency	$\eta_{\scriptscriptstyle T}$	38	45	_	%	$Pin = +8 dBm, V_{DD} = 4.8 V,$
2nd harmonic distortion	2nd H.D.	_	-45	-35	dBc	Pout = 2.8 W (At APC controlled)
3rd harmonic distortion	3rd H.D.		-45	-35	dBc	$R_L = Rg = 50\Omega$, $Tc = 25^{\circ}C$
Input VSWR	VSWR (in)	_	1.5	3.0	_	-
Output power (1)	Pout (1)	2.8	3.3	_	W	Pin = +8 dBm, V_{DD} = 4.8 V, V_{APC} = 2.5 V, R_{L} = Rg = $50Ω$, Tc = 25 °C
Output power (2)	Pout (2)	1.5	1.8	_	W	$Pin = +8 dBm, V_{DD} = 4 V,$ $V_{APC} = 2.5 V, R_{L} = Rg = 50Ω,$ Tc = 85°C
Isolation	_		-35	-20	dBm	$Pin = +12.5 dBm, V_{DD} = 4.8 V,$ $V_{APC} = 0.1 V, R_{L} = Rg = 50Ω,$ Tc = 25°C
Switching time	t _r , t _f	_	1	2	μs	Pin = +8 dBm, V_{DD} = 4.8 V, R_{L} = Rg = 50Ω, Tc = 25°C Time from Pout = -10 to +34.5 dBm
Stability	_	No pa oscilla	arasitic ation		_	Pin = +8 dBm, V_{DD} = 7 V, Pout \leq 2.8 W (At APC controlled), Rg = 50 Ω , Tc = 25°C, Output VSWR = 8 : 1 All phases

Package Dimensions



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